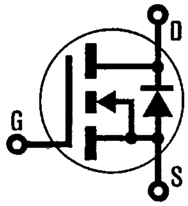
Data Sheet No. PD-9.357E

T-39-09

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFF330 IRFF331 IRFF332 IRFF333

N-CHANNEL POWER MOSFETs TO-39 PACKAGE



400 Volt, 1.0 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

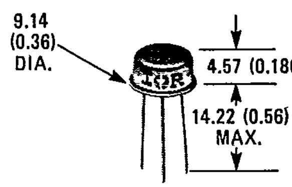
Features:

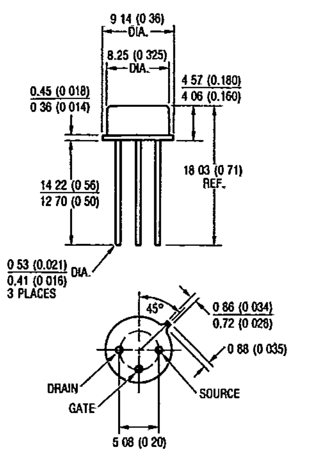
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFF330	400V	1.0Ω	3.5A
IRFF331	350V	1.0Ω	3.5A
IRFF332	400V	1.5Ω	3.0A
IRFF333	350V	1.5Ω	3.0A

CASE STYLE AND DIMENSIONS





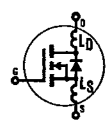
Conforms to JEDEC Outline TO-205AF (TO-39)
Dimensions in Millimeters and (Inches)

TO-39

Absolute Maximum Ratings

	Parameter	IRFF330	IRFF331	IRFF332	IRFF333	Units
V_{DS}	Drain — Source Voltage ①	400	350	400	350	V
V_{DGR}	Drain — Gate Voltage (R_{GS} = 20 kΩ)①	400	350	400	350	V
I_D @ T_C = 25°C	Continuous Drain Current	3.5	3.5	3.0	3.0	A
I_{DM}	Pulsed Drain Current ③	14	14	12	12	A
V_{GS}	Gate — Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	25 (See Fig. 14)				W
	Linear Derating Factor	0.2 (See Fig. 14)				W/K ④
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 14	14	12	12	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

	Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain — Source Breakdown Voltage	IRFF330 IRFF332	400	—	—	V	V_{GS} = 0V
		IRFF331 IRFF333	350	—	—	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate — Source Leakage Forward	ALL	—	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate — Source Leakage Reverse	ALL	—	—	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			—	—	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFF330 IRFF331	3.5	—	—	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., V_{GS} = 10V
		IRFF332 IRFF333	3.0	—	—	A	
$R_{DS(on)}$	Static Drain — Source On-State Resistance ②	IRFF330 IRFF331	—	0.8	1.0	Ω	V_{GS} = 10V, I_D = 2.0A
		IRFF332 IRFF333	—	1.0	1.5	Ω	
g_{fs}	Forward Transconductance ②	ALL	2.0	3.5	—	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., I_D = 2.0A
C_{iss}	Input Capacitance	ALL	—	700	900	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	—	150	300	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	—	40	80	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	—	—	30	ns	V_{DD} = 175V, I_D = 2.0A, Z_o = 15Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	—	—	35	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	—	55	ns	
t_f	Fall Time	ALL	—	—	35	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	18	30	nC	V_{GS} = 10V, I_D = 7.0A, V_{DS} = 0.8V Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	—	11	—	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	—	7.0	—	nC	
L_D	Internal Drain Inductance	ALL	—	5.0	—	nH	Measured from the drain lead, 5mm (0.2 in.) from header to center of die. — Modified MOSFET symbol showing the internal device inductances. 
L_S	Internal Source Inductance	ALL	—	15	—	nH	Measured from the source lead, 5mm (0.2 in.) from header to source bonding pad.

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	—	—	5.0	K/W ④	
R_{thJA}	Junction-to-Ambient	ALL	—	—	175	K/W ④	Typical socket mount

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFF330 IRFF331	—	—	3.5	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFF332 IRFF333	—	—	3.0	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFF330 IRFF331	—	—	14	A	
		IRFF332 IRFF333	—	—	12	A	
V_{SD}	Diode Forward Voltage ②	IRFF330 IRFF331	—	—	1.6	V	$T_C = 25°C, I_S = 3.5A, V_{GS} = 0V$
		IRFF332 IRFF333	—	—	1.5	V	$T_C = 25°C, I_S = 3.0A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	—	600	—	ns	$T_J = 150°C, I_F = 3.5A, dI_F/dt = 100A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	—	4.0	—	μC	$T_J = 150°C, I_F = 3.5A, dI_F/dt = 100A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① $T_J = 25°C$ to $150°C$. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).
④ K/W = °C/W
W/K = W/°C

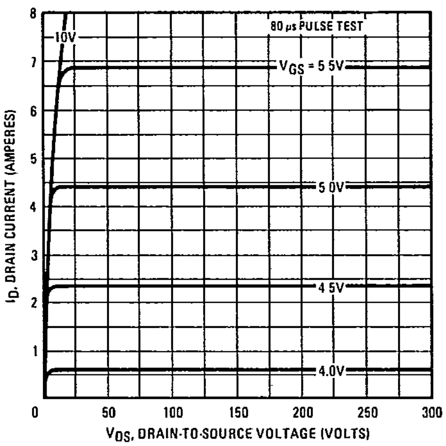


Fig. 1 — Typical Output Characteristics

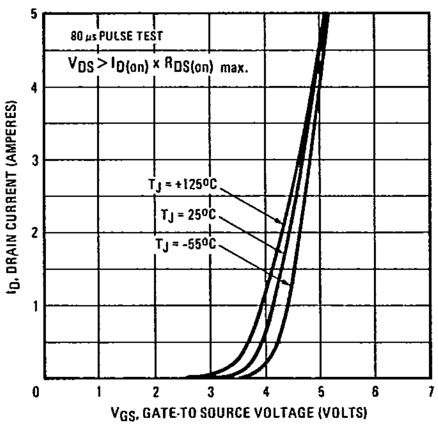


Fig. 2 — Typical Transfer Characteristics

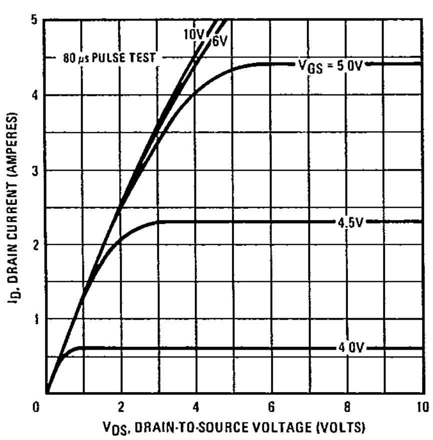


Fig. 3 — Typical Saturation Characteristics

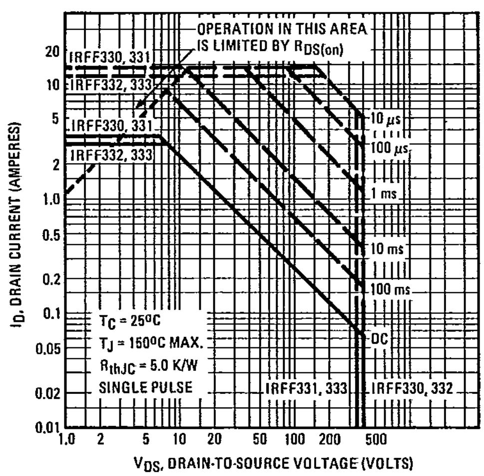


Fig. 4 — Maximum Safe Operating Area

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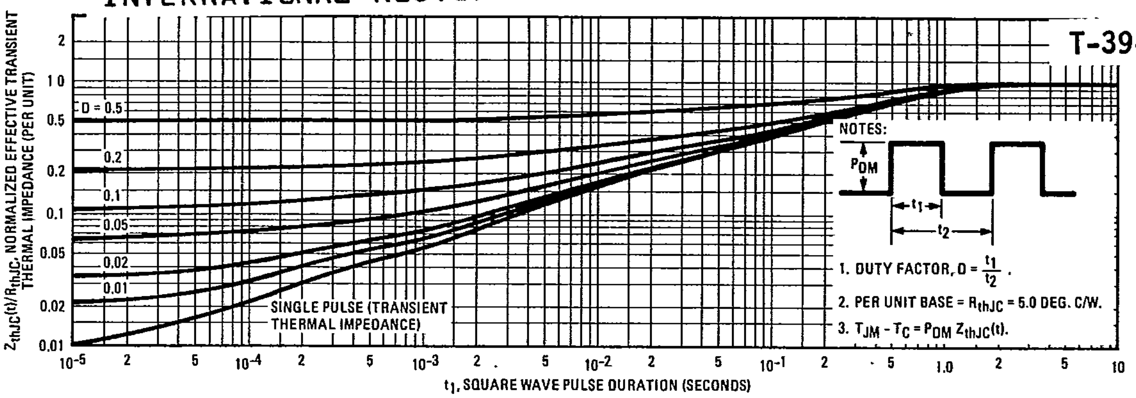

Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

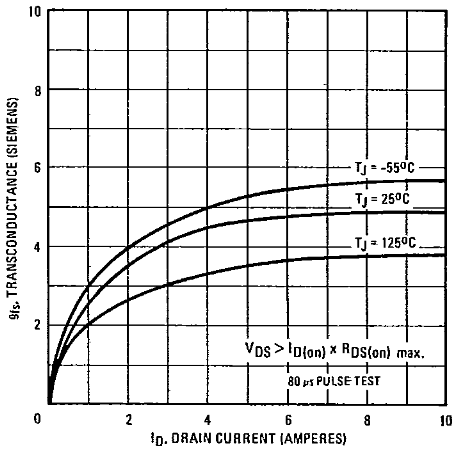

Fig. 6 — Typical Transconductance Vs. Drain Current

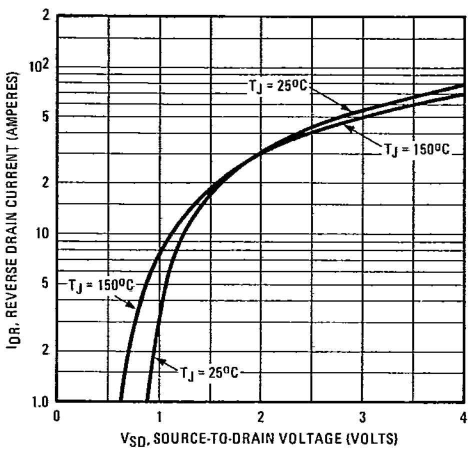

Fig. 7 — Typical Source-Drain Diode Forward Voltage

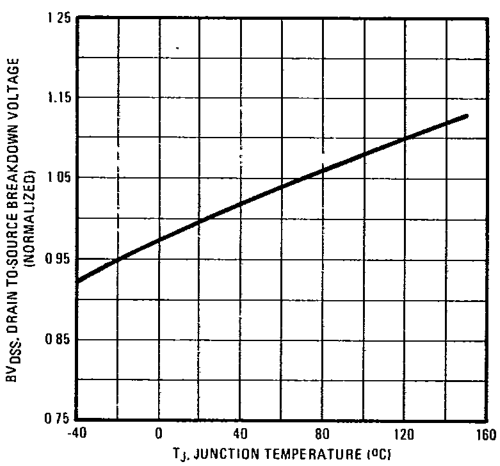

Fig. 8 — Breakdown Voltage Vs. Temperature

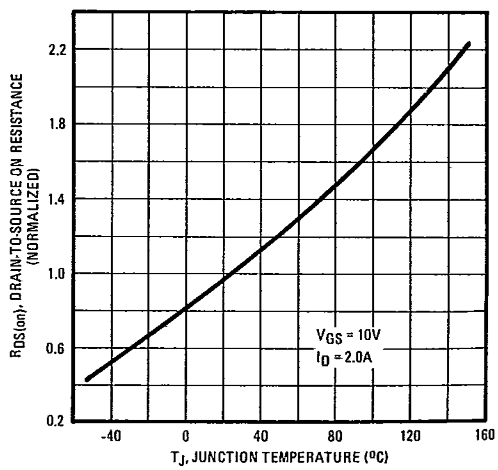

Fig. 9 — Normalized On-Resistance Vs. Temperature

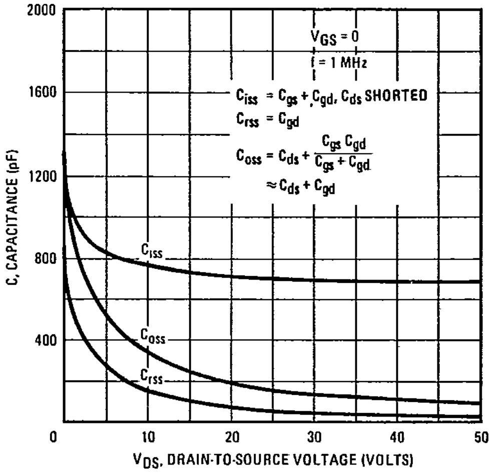

Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

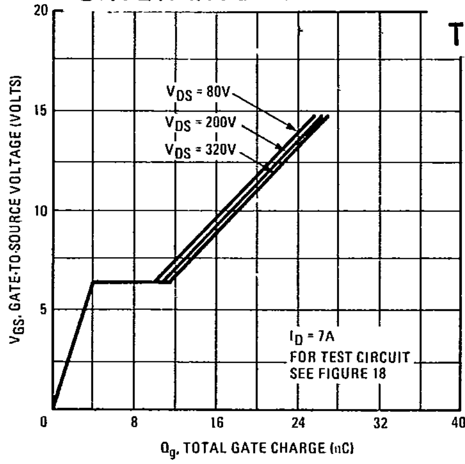

Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

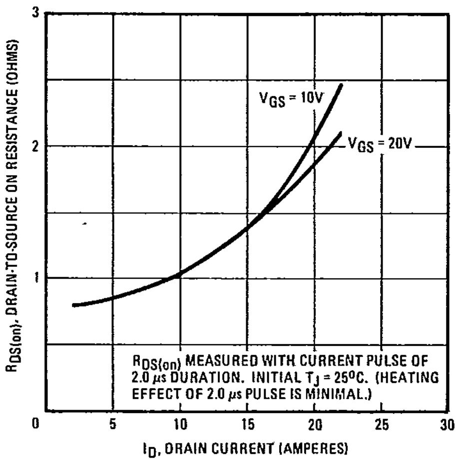

Fig. 12 — Typical On-Resistance Vs. Drain Current

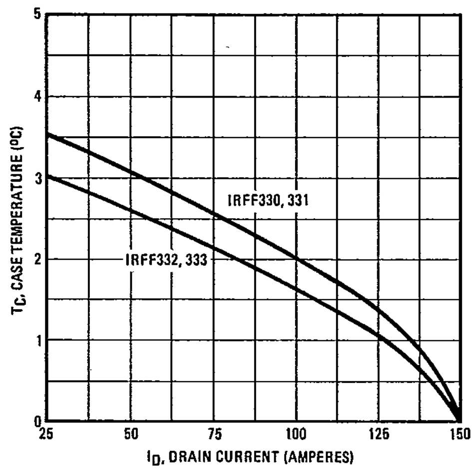

Fig. 13 — Maximum Drain Current Vs. Case Temperature

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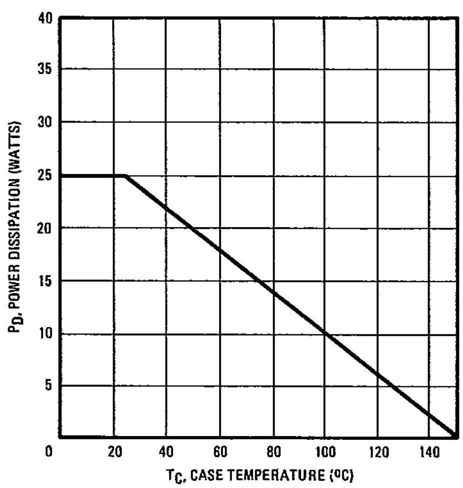

Fig. 14 — Power Vs. Temperature Derating Curve

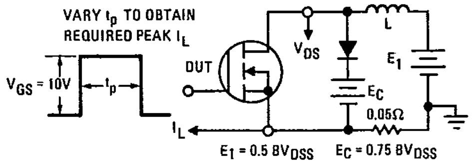

Fig. 15 – Clamped Inductive Test Circuit

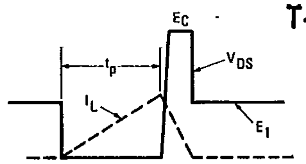

Fig. 16 – Clamped Inductive Waveforms

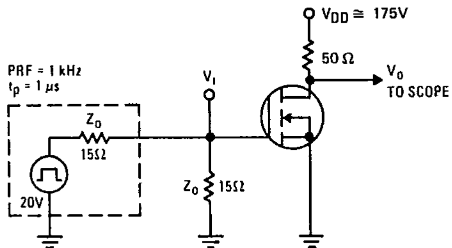

Fig. 17 – Switching Time Test Circuit

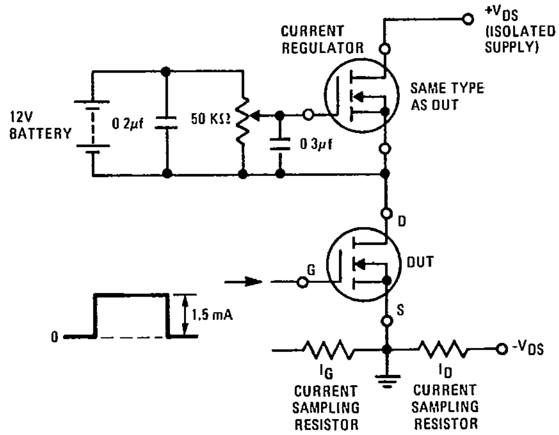

Fig. 18 – Gate Charge Test Circuit

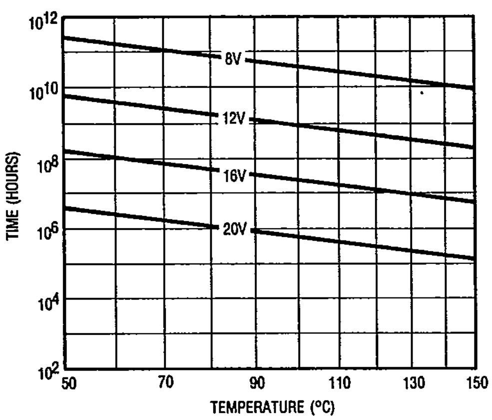

*Fig. 19 – Typical Time to Accumulated 1% Gate Failure

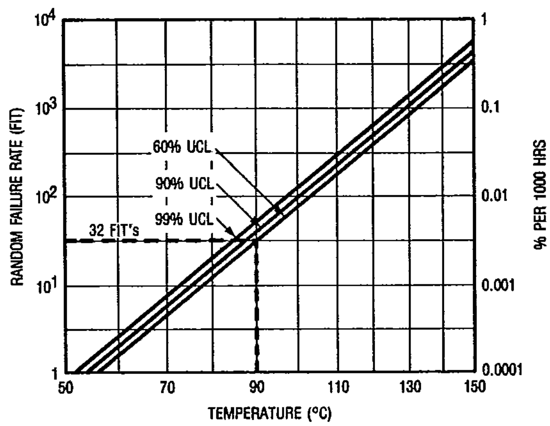

Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.